BLC9G20LS-470AVT

Power LDMOS transistor Rev. 3 — 24 November 2017

AMMPLEON

Product data sheet

Product profile 1.

1.1 General description

470 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 1805 MHz to 1990 MHz.

Typical performance

Typical RF performance at $T_{case} = 25$ °C in an asymmetrical Doherty production test circuit. V_{DS} = 28 V; I_{Dq} = 500 mA (main); $V_{GS(amp)peak}$ = 0.5 V, unless otherwise specified.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	η _D	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	1805 to 1880	28	80	16	49	-35 <u>[1]</u>

^[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01% probability on CCDF per carrier.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Designed for broadband operation (1805 MHz to 1990 MHz)
- Asymmetric design to achieve optimum efficiency across the band
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 1805 MHz to 1990 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain2 (peak)			0.7
2	drain1 (main)		7 2 1 6	2, 7
3	gate1 (main)		5	
4	gate2 (peak)		3 4	3——5
5	source	[1]		4—
6	video decoupling (peak)			' ⊢ ¬
7	video decoupling (main)			1, 6 aaa-014884

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage					
	Name	Description	Version				
BLC9G20LS-470AVT	-	air cavity plastic earless flanged package; 6 leads	SOT1258-1				

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage		-	65	V
V _{GS(amp)main}	main amplifier gate-source voltage		-5	+13	V
V _{GS(amp)peak}	peak amplifier gate-source voltage		-5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	<u>[1]</u>	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}		V_{DS} = 28 V; I_{Dq} = 400 mA (main); $V_{GS(amp)peak}$ = 0.5 V; T_{case} = 80 °C		
		$P_L = 49 \text{ dBm}$	0.26	K/W
		$P_L = 51 \text{ dBm}$	0.20	K/W

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice				1	
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.44 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 144 mA	1.5	2	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 30 V; I _D = 864 mA	1.8	2.1	2.35	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	31.5	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	280	nA
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 5.04 A	-	10.2	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 5.04 \text{ A}$	-	99	165	mΩ
Peak dev	rice					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.6 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 260 mA	1.5	2	2.5	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 30 V; I _D = 1560 mA	1.4	1.85	2.25	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	2.8	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	49	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	280	nA
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 9.1 A	-	17.3	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 9.1 \text{ A}$	-	51	85	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; RF performance at V_{DS} = 28 V; I_{Dq} = 400 mA (main); $V_{GS(amp)peak}$ = 0.5 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1805 MHz to 1880 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G_p	power gain	P _{L(AV)} = 80 W	14.5	15.7	-	dB
RLin	input return loss	P _{L(AV)} = 80 W	-	-10	-6	dB
η_{D}	drain efficiency	P _{L(AV)} = 80 W	42.5	47.5	-	%
ACPR	adjacent channel power ratio	P _{L(AV)} = 80 W	-	-33	-28	dBc

Table 8. RF characteristics

Test signal: pulsed CW; t_p = 100 μ s; δ = 10 %; RF performance at V_{DS} = 28 V; I_{Dq} = 400 mA (main); $V_{GS(amp)peak}$ = 0.5 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 1805 MHz to 1880 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P _{L(M)}	peak output power		380	425	-	W

7. Test information

7.1 Ruggedness in Doherty operation

The BLC9G20LS-470AVT is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 400 mA (main); $V_{GS(amp)peak}$ = 0.5 V; P_L = 250 W (CW); f = 1805 MHz.

7.2 Impedance information

Table 9. Typical impedance of main device Measured load-pull data of main device; $I_{Dq} = 400 \text{ mA (main)}$; $V_{DS} = 28 \text{ V}$.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum po	Maximum power load									
1805	1.03 – j4.87	1.22 – j3.6	206.0	60.0	15.16					
1843	2.10 - j4.50	1.22 – j3.6	200.0	60.0	14.93					
1880	1.58 – j5.07	1.22 – j3.6	200.4	60.3	15.34					
Maximum dr	ain efficiency load				•					
1805	1.03 – j4.87	2.31 – j2.74	142.5	68.12	17.44					
1843	2.10 - j4.50	2.08 – j2.55	137.0	68.24	17.06					
1880	1.58 – j5.07	1.90 – j2.76	146.0	67.8	17.30					

^[1] Z_S and Z_L defined in Figure 1.

Table 10. Typical impedance of peak device Measured load-pull data of peak device; $I_{Dq} = 1300 \text{ mA}$ (peak); $V_{DS} = 28 \text{ V}$.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum	Maximum power load									
1805	1.06 – j5.55	2.0 - j3.8	322.8	56.90	15.60					
1843	1.89 – j5.55	2.0 - j3.8	315.5	56.18	15.16					
1880	1.86 – j6.21	2.2 – j4.1	313.3	55.30	15.74					
Maximum o	drain efficiency loa	d			·					
1805	1.06 – j5.55	2.76 - j2.70	267.9	64.5	17.23					
1843	1.89 – j5.55	2.68 - j2.24	234.4	63.5	17.04					
1880	1.86 – j6.21	2.68 - j2.24	230.7	63.5	17.79					

^[1] Z_S and Z_L defined in Figure 1.

^[2] at 3 dB gain compression.

^[2] at 3 dB gain compression.

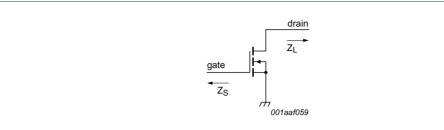


Fig 1. Definition of transistor impedance

7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load Measured load-pull data of main device; I_{Dq} = 400 mA (main); V_{DS} = 28 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [3]	G _p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
1805	1.03 – j4.87	1.83 – j3.50	52.6	46.5	19.1
1843	2.10 - j4.50	1.67 – j3.30	52.7	47.0	19.2
1880	1.58 – j5.07	1.50 – j3.12	52.8	48.1	19.4

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at $P_{L(AV)} = 49 \text{ dBm}$.

Table 12. Typical impedance of main device at 1: 2.5 load

Measured load-pull data of main device; I_{Dq} = 400 mA (main); V_{DS} = 28 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [3]	G _p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
1805	1.03 – j4.87	2.56 - j1.80	50.48	63.6	21.2
1843	2.10 - j4.50	2.84 - j1.96	50.46	64.0	21.4
1880	1.58 – j5.07	3.14 – j2.12	50.40	64.0	21.5

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at $P_{L(AV)} = 49 \text{ dBm}$.

7.4 Test circuit

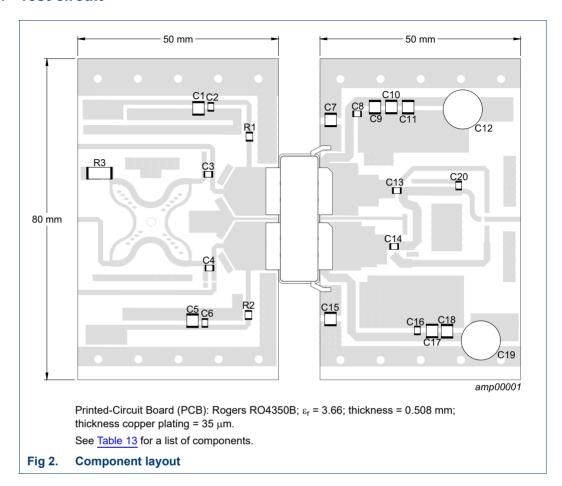


Table 13. List of components

See Figure 2 for component layout.

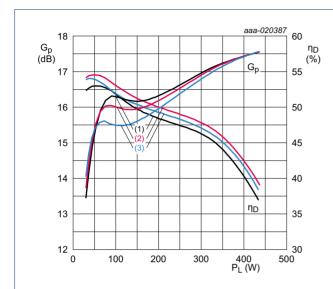
Component	Description	Value	Remarks
C1, C5, C7, C9, C10, C11, C15, C17, C18	multilayer ceramic chip capacitor	10 μF, 50 V	1
C2, C3, C4, C6, C8, C16	multilayer ceramic chip capacitor	36 pF	1
C12, C19	electrolytic capacitor	1000 μF, 63 V	
C13	multilayer ceramic chip capacitor	10 pF	1
C14	multilayer ceramic chip capacitor	27 pF	1
C20	multilayer ceramic chip capacitor	0.1 pF	1
R1, R2	resistor	5.1 Ω	SMD 0805
R3	resistor	50 Ω	SMD 0805

^[1] Murata or capacitor of same quality

[2] American Technical Ceramics type 600F or capacitor of same quality

7.5 Graphical data

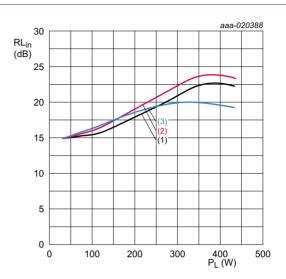
7.5.1 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 400 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values

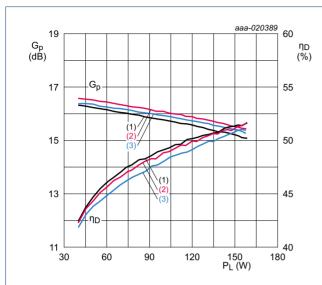


 V_{DS} = 28 V; I_{Dq} = 400 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 4. Input return loss as a function of output power; typical values

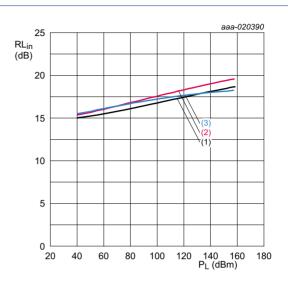
7.5.2 1-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 400 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

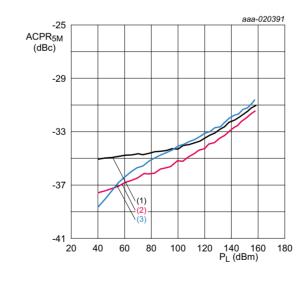
Fig 5. Power gain and drain efficiency as function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 400 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 6. Input return loss as a function of output power; typical values

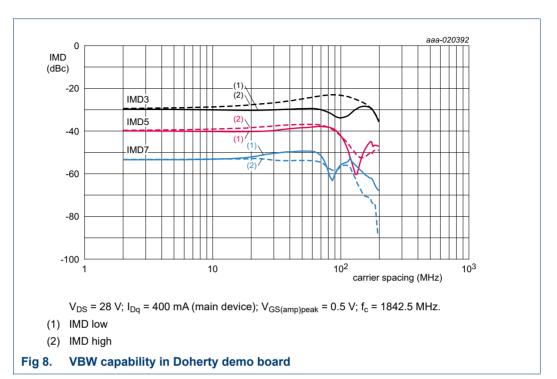


 V_{DS} = 28 V; I_{Dq} = 400 mA (main device); $V_{GS(amp)peak}$ = 0.5 V.

- (1) f = 1805 MHz
- (2) f = 1842.5 MHz
- (3) f = 1880 MHz

Fig 7. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

7.5.3 2-Tone VBW



8. Package outline

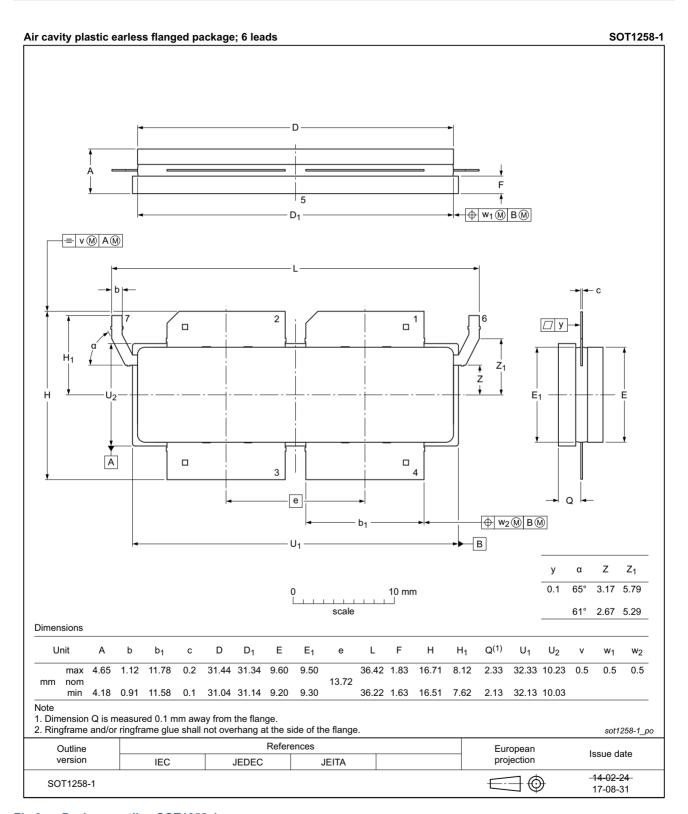


Fig 9. Package outline SOT1258-1

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

10. Abbreviations

Table 15. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9G20LS-470AVT v.3	20171124	Product data sheet	-	BLC9G20LS-470AVT v.2
Modifications:	<u>Table 2 on page 2</u> : changed simplified version drawing SOT1258-3 to SOT1258-1			
	Table 3 on pa	ige 2: changed version SOT1	258-3 to SOT1258-1	
	• Figure 2 on p	age 6: updated figure		
	• Figure 9 on p	age 10: changed package ou	tline drawing SOT12	58-3 to SOT1258-1
BLC9G20LS-470AVT v.2	20161202	Product data sheet	-	BLC9G20LS-470AVT v.1
BLC9G20LS-470AVT v.1	20160224	Product data sheet	-	-

BLC9G20LS-470AVT

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BLC9G20LS-470AVT

Power LDMOS transistor

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